Semiconductor Nanocrystal Optoelectronics using Colloidal Quantum Wells for Lighting and Displays: *Pushing the Limits, Breaking Records*

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Lighting and displays are integral parts of human activities and economic development. Semiconductor nanocrystals, now offering a market volume exceeding 1 Billion Euros annually, have attracted great interest in guality lighting and displays in the last decade. Such colloidal semiconductors enable enriched color conversion essential to superior lighting and displays. These colloids span different types and heterostructures of semiconductors, starting in the form of colloidal quantum dots about three decades ago and extending to the latest sub-family of nanocrystals, the colloidal quantum wells, in the last decade. In this talk, we will present most recent examples of photonic structures and device architectures using the colloidal guantum wells [1-5] for lighting and displays. Also, we will present a powerful, large-area, orientation-controlled selfassembly technique for orienting these colloidal guantum wells either all face down or all edge up [6]. We will demonstrate three-dimensional constructs of their oriented selfassemblies with monolayer precision [7]. Among their extraordinary features important to applications in lighting and displays, we will show record high efficiency from their colloidal LEDs [8] and record gain coefficients from their colloidal laser media [9] using heterostructures [2-5] and/or oriented assemblies [6,7] of colloidal quantum wells. Given their current accelerating progress, these solution-processed quantum wells hold great promise to challenge their epitaxial thin-film counterparts in semiconductor optoelectronics in the near future.

References

- [1] B. Guzelturk et al., HVD, Nano Letters 19, 277 (2019)
- [2] Y. Altıntas et al., HVD, ACS Nano 13, 10662 (2019)
- [3] N. Taghipour et al., HVD, Nature Communications 11, 3305 (2020)
- [4] F. Shabani et al., HVD, Small 18, 2106115 (2022)
- [5] E. G. Durmusoglu et al., HVD, ACS Nano in press (2023)
- [6] O. Erdem et al., HVD, Nano Letters 19, 4297 (2019)
- [7] O. Erdem et al., HVD, Nano Letters 20, 6459 (2020)
- [8] B. Liu et al., HVD, Advanced Materials 32, 1905824 (2020)
- [9] J. Maskoun et al., HVD, Advanced Materials 33, 2007131 (2021)